

CMOD6001

**SURFACE MOUNT  
ULTRA LOW LEAKAGE  
SILICON SWITCHING DIODE**



[www.centrasemi.com](http://www.centrasemi.com)

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMOD6001 type is a silicon switching diode manufactured by the epitaxial planar process, epoxy molded in a ULTRAmimi™ surface mount package, designed for switching applications requiring an extremely low leakage diode.

**MARKING CODE: 61**

ULTRAmimi™



**SOD-523 CASE**

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

Continuous Reverse Voltage
Peak Repetitive Reverse Voltage
Continuous Forward Current
Peak Repetitive Forward Current
Peak Forward Surge Current, $t_p=1.0\mu\text{s}$
Peak Forward Surge Current, $t_p=1.0\text{s}$
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

**SYMBOL**

$V_R$	75
$V_{RRM}$	100
$I_F$	250
$I_{FRM}$	250
$I_{FSM}$	4.0
$I_{FSM}$	1.0
$P_D$	250
$T_J, T_{stg}$	-65 to +150
$\theta_{JA}$	500

**UNITS**

V
V
mA
mA
A
A
mW
$^\circ\text{C}$
$^\circ\text{C}/\text{W}$

**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

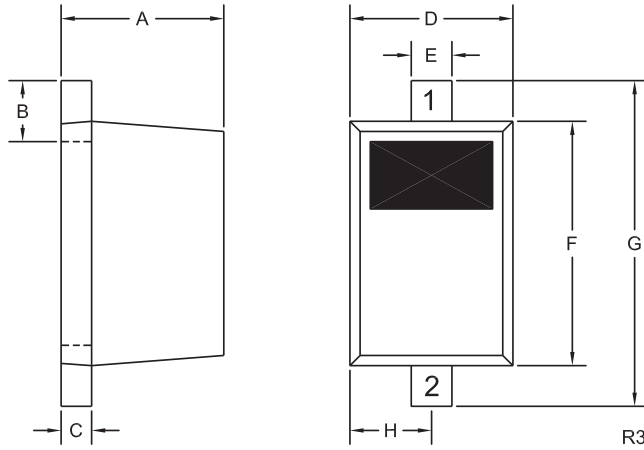
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$I_R$	$V_R=75\text{V}$		500	pA
$BV_R$	$I_R=100\mu\text{A}$	100		V
$V_F$	$I_F=1.0\text{mA}$		0.85	V
$V_F$	$I_F=10\text{mA}$		0.95	V
$V_F$	$I_F=100\text{mA}$		1.1	V
$C_T$	$V_R=0, f=1.0\text{MHz}$		2.0	pF
$t_{rr}$	$I_R=I_F=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$		3.0	$\mu\text{s}$

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SOD-523 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) Cathode
- 2) Anode

MARKING CODE: 61

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.020	0.031	0.50	0.80
B	0.008	0.016	0.20	0.40
C	0.002	0.008	0.05	0.20
D	0.028	0.035	0.70	0.90
E	0.008	0.014	0.20	0.35
F	0.039	0.055	1.00	1.40
G	0.055	0.071	1.40	1.80
H	0.016		0.40	

SOD-523 (REV: R3)

R6 (9-May 2011)